

**NPN Silicon Epitaxial Planar Transistor****S9013****FEATURES**

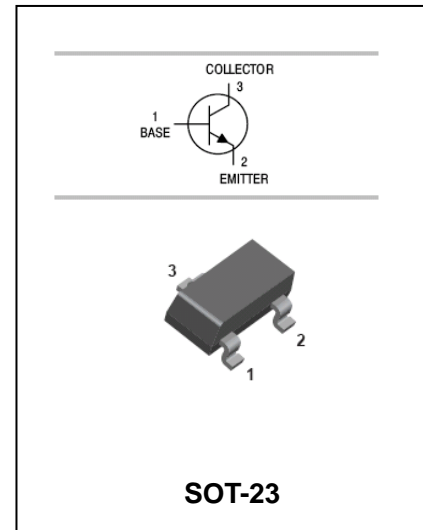
- High Collector Current.( $I_C=500\text{mA}$ ).
- Complementary To S9012.
- Excellent  $H_{FE}$  Linearity.
- Power dissipation.( $P_C=300\text{mW}$ ).



Lead-free

**APPLICATIONS**

- High Collector Current.

**ORDERING INFORMATION**

Type No.	Marking	Package Code
S9013	J3	SOT-23

**MAXIMUM RATING @  $T_a=25^\circ\text{C}$  unless otherwise specified**

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	40	V
$V_{CEO}$	Collector-Emitter Voltage	25	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	500	mA
$P_C$	Collector Dissipation	300	mW
$T_j, T_{stg}$	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

**NPN Silicon Epitaxial Planar Transistor****S9013****ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1mA, I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40V, I_E=0$			0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE}=20V, I_B=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=1V, I_C=50mA$	120		400	
		$V_{CE}=1V, I_C=500mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500mA, I_B=50mA$			1.2	V
Transition frequency	$f_T$	$V_{CE}=6V, I_C=20mA$ $f=30MHz$	150			MHz

**CLASSIFICATION OF  $h_{FE(1)}$** 

Rank	L	H	J
Range	120-200	200-350	300-400



# NPN Silicon Epitaxial Planar Transistor

# S9013

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

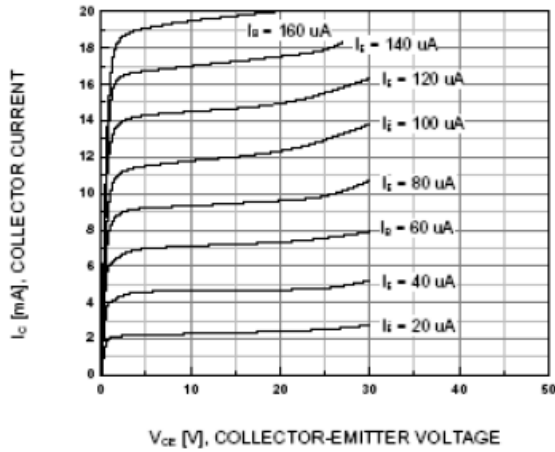


Figure 1. Static Characteristic

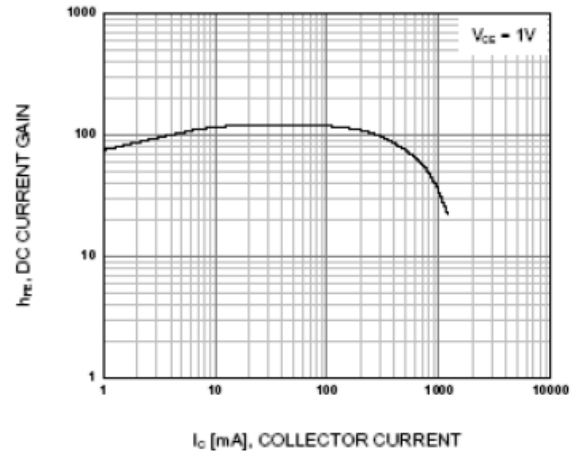


Figure 2. DC current Gain

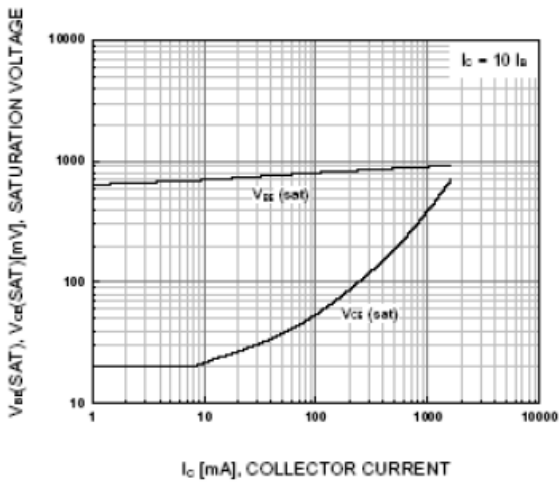


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

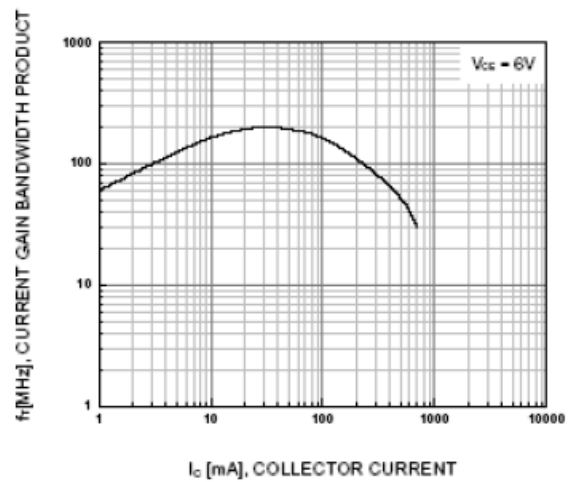


Figure 4. Current Gain Bandwidth Product



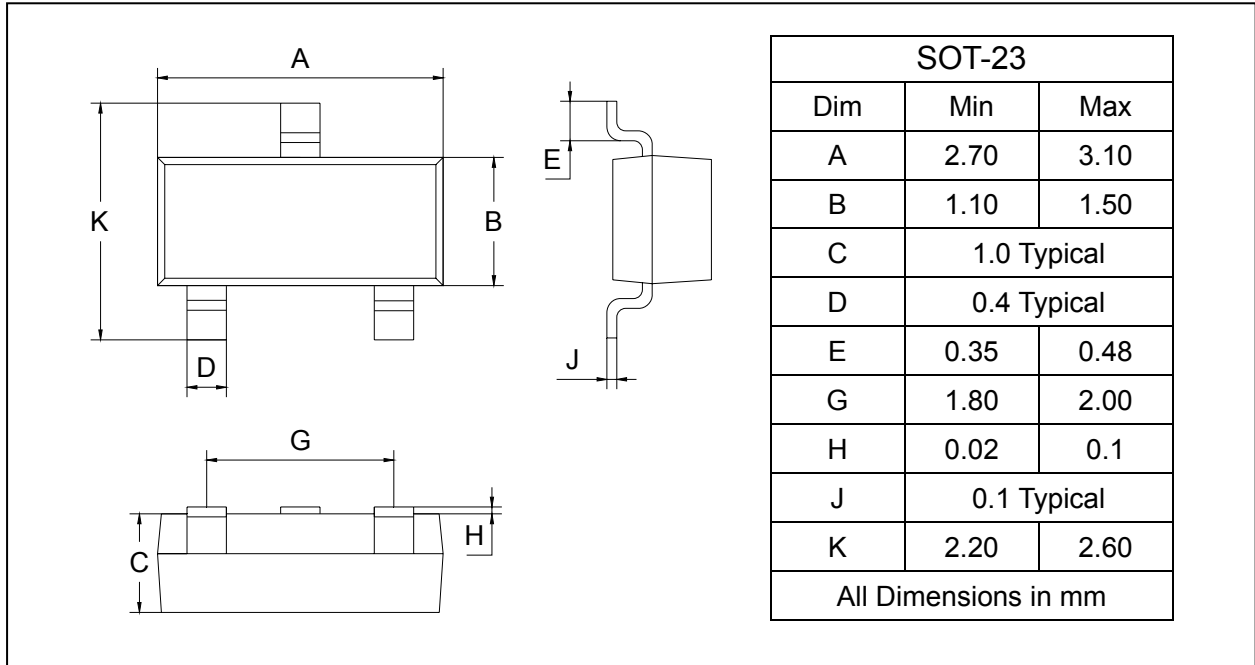
# NPN Silicon Epitaxial Planar Transistor

# S9013

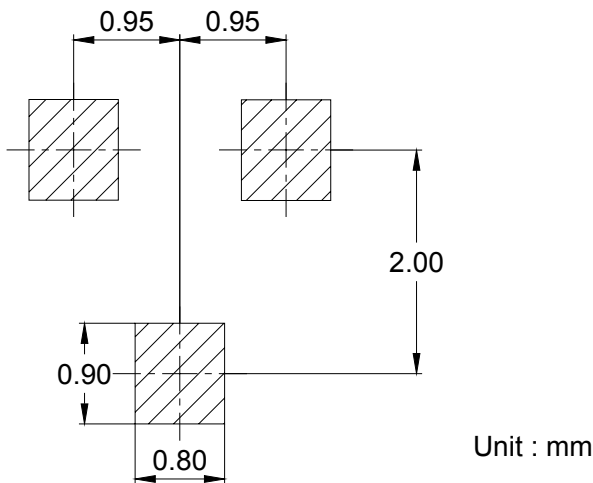
## PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



## SOLDERING FOOTPRINT



## PACKAGE INFORMATION

Device	Package	Shipping
S9013	SOT-23	3000/Tape&Reel

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [Bipolar Transistors - BJT category](#):*

*Click to view products by [LangJie manufacturer](#):*

Other Similar products are found below :

[BC559C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [NJVMJD148T4G](#) [NTE16](#) [NTE195A](#) [IMX9T110](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SB1204S-TL-E](#) [2SC5488A-TL-H](#) [FMC5AT148](#) [2N2369ADCSM](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC4618TLN](#) [CPH6501-TL-E](#) [US6T6TR](#) [BAX18/A52R](#) [BC556/112](#) [IMZ2AT108](#) [MMST8098T146](#) [MCH6102-TL-E](#) [BC846B-13-F](#) [2N3879](#) [30A02MH-TL-E](#) [NTE13](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [JANTX2N2920L](#) [JANSR2N2907AUB](#) [CMLT3946EG TR](#) [SNSS40600CF8T1G](#) [CMLT3906EG TR](#) [GRP-DATA-JANS2N2907AUB](#) [GRP-DATA-JANS2N2222AUA](#) [MMDT3946FL3-7](#) [2N4240](#) [JANS2N3019](#) [MSB30KH-13](#) [2N2221AUB](#) [2SD1815T-TL-E](#) [2N6678](#) [2N2907Ae4](#) [JAN2N3507](#)